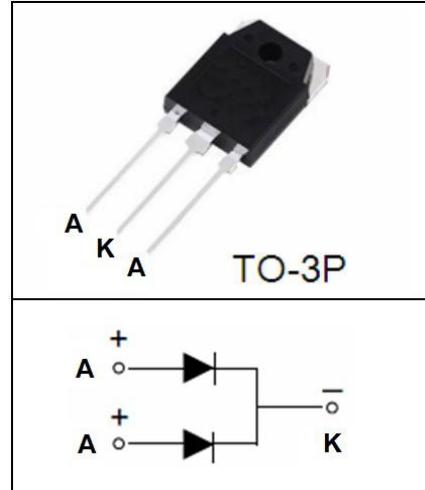


**MBR30100PT****Dual High Voltage Schottky Rectifier****●Features:**

- Common Cathode Structure
 - Low Power Loss and High Efficiency
 - Low Forward Voltage Drop
 - High Surge Capability
- Application:**
- High Frequency Switch
 - Free Wheeling, and Polarity Protection Applications

**Absolute Maximum Ratings(Tc=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	100	V
V _R	Maximum DC Reverse Voltage	100	V
I _{F(AV)}	Average Rectified Forward Current, Tc=120°C	15(Per Leg) 30(Per Device)	A
I _{FSM}	Peak Forward Surge Current, 8.3ms Half Sine wave	250	A
T _j	Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55 to +150	°C

Thermal Characteristics(Tc=25°C unless otherwise noted)

Symbol	Parameter	Max	Unit
R _{θJC}	Thermal Resistance, Junction to Case Per Leg	1.4	°C /W
R _{θJA}	Thermal Resistance, Junction to Ambient Per Leg	59	°C /W

Electrical Characteristics(Tc=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Max	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	I _R =100μA	100		V
I _R	Reverse Current	V _R =100V Tc=25°C V _R =100V Tc=125°C		0.1 5	mA
V _F	Forward Voltage	I _F =15A Tc=25°C I _F =15A Tc=125°C I _F =30A Tc=25°C I _F =30A Tc=125°C		0.88 0.78 1.05 0.95	V



MBR30100PT

Dual High Voltage Schottky Rectifier

Typical Performance Characteristics

Figure 1. Forward Current Characteristics

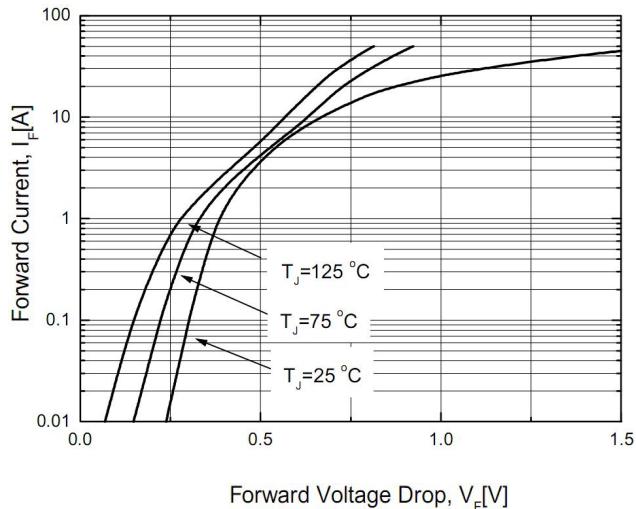


Figure 2. Reverse Leakage Current

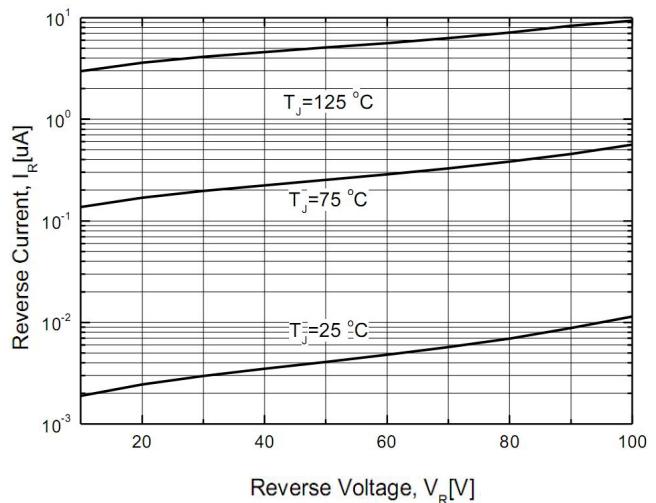


Figure 3. Junction Capacitance

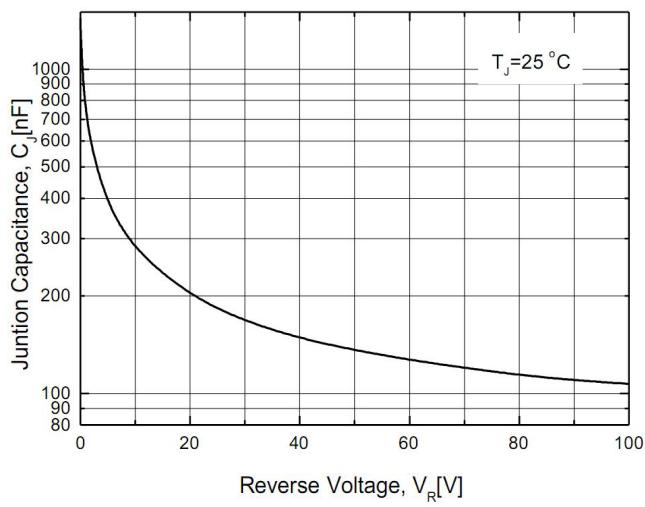
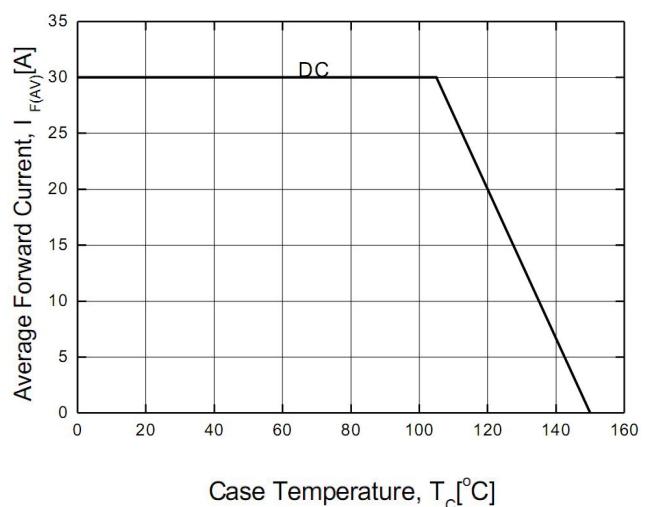


Figure 4. Power Derating





MBR30100PT

Dual High Voltage Schottky Rectifier

TO-3P Package Dimensions

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	4.40		5.10	E	15.20		16.20
A1	1.40	1.50	1.70	E1		13.60	
A2	2.10	2.40	2.70	E2		9.60	
b	0.80	1.00	1.20	e	5.15	5.45	5.75
b1	1.90		2.30	L	19.00	20.00	21.00
b2	2.90		3.30	L1	2.50		3.50
C	0.45	0.60	0.75	Q		5.10	
D	19.40	19.90	20.40	Q1		3.90	
D1		13.90					

